

**MICROCHIP**

25AA160/25LC160/25C160

16K SPI™ Bus Serial EEPROM

DEVICE SELECTION TABLE

Part Number	Vcc Range	Max Clock Frequency	Temp Ranges
25C160	4.5-5.5V	3 MHz	C,I,E
25LC160	2.5-5.5V	2 MHz	C,I
25AA160	1.8-5.5V	1 MHz	C,I

FEATURES

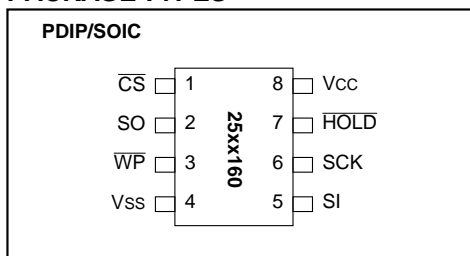
- Low power CMOS technology
 - Write current: 3 mA maximum
 - Read current: 500 μ A typical
 - Standby current: 500 nA typical
- 2048 x 8 bit organization
- 16 byte page
- Write cycle time: 5ms max.
- Self-timed ERASE and WRITE cycles
- Block write protection
 - Protect none, 1/4, 1/2, or all of array
- Built-in write protection
 - Power on/off data protection circuitry
 - Write enable latch
 - Write protect pin
- Sequential read
- High reliability
 - Endurance: 1M cycles (guaranteed)
 - Data retention: > 200 years
 - ESD protection: > 4000 V
- 8-pin PDIP and SOIC packages
- Temperature ranges supported:
 - Commercial (C): 0°C to +70°C
 - Industrial (I): -40°C to +85°C
 - Automotive (E) (25C160): -40°C to +125°C

DESCRIPTION

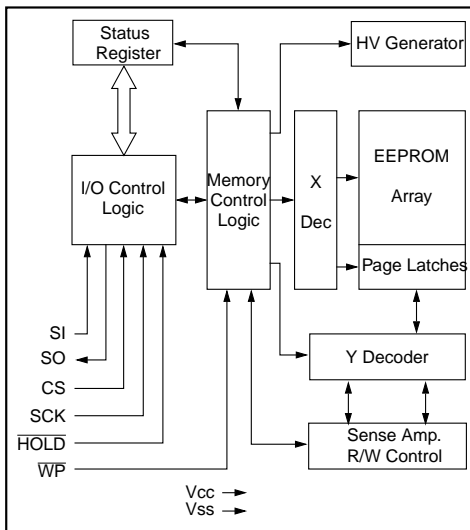
The Microchip Technology Inc. 25AA160/25LC160/25C160 (25xx160*) are 16K bit serial Electrically Erasable PROMs. The memory is accessed via a simple Serial Peripheral Interface (SPI) compatible serial bus. The bus signals required are a clock input (SCK) plus separate data in (SI) and data out (SO) lines. Access to the device is controlled through a chip select (CS) input.

Communication to the device can be paused via the hold pin (HOLD). While the device is paused, transitions on its inputs will be ignored, with the exception of chip select, allowing the host to service higher priority interrupts.

PACKAGE TYPES



BLOCK DIAGRAM



*25xx160 is used in this document as a generic part number for the 25AA160/25LC160/25C160 devices.

SPI is a trademark of Motorola.

25AA160/25LC160/25C160

1.0 ELECTRICAL CHARACTERISTICS

1.1 Maximum Ratings*

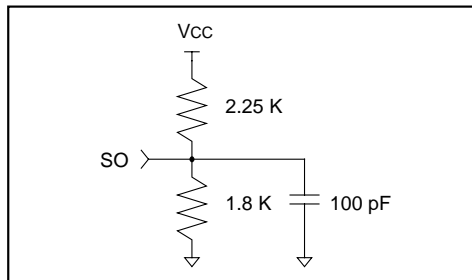
V_{CC}7.0V
 All inputs and outputs w.r.t. V_{SS}-0.6V to V_{CC}+1.0V
 Storage temperature -65°C to 150°C
 Ambient temperature under bias -65°C to 125°C
 Soldering temperature of leads (10 seconds) +300°C
 ESD protection on all pins4kV

***Notice:** Stresses above those listed under 'Maximum ratings' may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for an extended period of time may affect device reliability

TABLE 1-1: PIN FUNCTION TABLE

Name	Function
\overline{CS}	Chip Select Input
SO	Serial Data Output
SI	Serial Data Input
SCK	Serial Clock Input
\overline{WP}	Write Protect Pin
V _{SS}	Ground
V _{CC}	Supply Voltage
\overline{HOLD}	Hold Input

FIGURE 1-1: AC TEST CIRCUIT



1.2 AC Test Conditions

AC Waveform:

V_{LO} = 0.2V

V_{HI} = V_{CC} - 0.2V (Note 1)

V_{HI} = 4.0V (Note 2)

Timing Measurement Reference Level

Input 0.5 V_{CC}

Output 0.5 V_{CC}

Note 1: For V_{CC} ≤ 4.0V

2: For V_{CC} > 4.0V

TABLE 1-2: DC CHARACTERISTICS

All parameters apply over the specified operating ranges unless otherwise noted.					
Commercial (C): T _{AMB} = 0°C to +70°C V _{CC} = 1.8V to 5.5V					
Industrial (I): T _{AMB} = -40°C to +85°C V _{CC} = 1.8V to 5.5V					
Automotive (E): T _{AMB} = -40°C to +125°C V _{CC} = 4.5V to 5.5V (25C160 only)					
Parameter	Symbol	Min	Max	Units	Test Conditions
High level input voltage	V _{IH1}	2.0	V _{CC} +1	V	V _{CC} ≥ 2.7V (Note)
	V _{IH2}	0.7 V _{CC}	V _{CC} +1	V	V _{CC} < 2.7V (Note)
Low level input voltage	V _{IL1}	-0.3	0.8	V	V _{CC} ≥ 2.7V (Note)
	V _{IL2}	-0.3	0.3 V _{CC}	V	V _{CC} < 2.7V (Note)
Low level output voltage	V _{OL}	—	0.4	V	I _{OL} = 2.1 mA
	V _{OL}	—	0.2	V	I _{OL} = 1.0 mA, V _{CC} < 2.5V
High level output voltage	V _{OH}	V _{CC} -0.5	—	V	I _{OH} = -400 μA
Input leakage current	I _{LI}	-10	10	μA	\overline{CS} = V _{CC} , V _{IN} = V _{SS} TO V _{CC}
Output leakage current	I _{LO}	-10	10	μA	\overline{CS} = V _{CC} , V _{OUT} = V _{SS} TO V _{CC}
Internal Capacitance (all inputs and outputs)	C _{INT}	—	7	pF	T _{AMB} = 25°C, CLK = 1.0 MHz, V _{CC} = 5.0V (Note)
Operating Current	I _{CC} Read	—	1	mA	V _{CC} = 5.5V; F _{CLK} =3.0 MHz; SO = Open
		—	500	μA	V _{CC} = 2.5V; F _{CLK} =2.0 MHz; SO = Open
	I _{CC} Write	—	5	mA	V _{CC} = 5.5V
		—	3	mA	V _{CC} = 2.5V
Standby Current	I _{CCS}	—	5	μA	\overline{CS} = V _{CC} = 5.5V, Inputs tied to V _{CC} or V _{SS}
		—	1	μA	\overline{CS} = V _{CC} = 2.5V, Inputs tied to V _{CC} or V _{SS}

Note: This parameter is periodically sampled and not 100% tested.

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TABLE 1-3: AC CHARACTERISTICS

All parameters apply over the specified operating ranges unless otherwise noted.		Commercial (C): Industrial (I): Automotive (E):		Tamb = 0°C to +70°C Tamb = -40°C to +85°C Tamb = -40°C to +125°C	VCC = 1.8V to 5.5V VCC = 1.8V to 5.5V VCC = 4.5V to 5.5V (25C160 only)
Parameter	Symbol	Min	Max	Units	Test Conditions
Clock Frequency	FCLK	—	3	MHz	VCC = 4.5V to 5.5V
		—	2	MHz	VCC = 2.5V to 4.5V
		—	1	MHz	VCC = 1.8V to 2.5V
CS Setup Time	TCSS	100	—	ns	VCC = 4.5V to 5.5V
		250	—	ns	VCC = 2.5V to 4.5V
		500	—	ns	VCC = 1.8V to 2.5V
CS Hold Time	TCSH	150	—	ns	VCC = 4.5V to 5.5V
		250	—	ns	VCC = 2.5V to 4.5V
		475	—	ns	VCC = 1.8V to 2.5V
CS Disable Time	TCSD	500	—	ns	
Data Setup Time	TSU	30	—	ns	VCC = 4.5V to 5.5V
		50	—	ns	VCC = 2.5V to 4.5V
		50	—	ns	VCC = 1.8V to 2.5V
Data Hold Time	THD	50	—	ns	VCC = 4.5V to 5.5V
		100	—	ns	VCC = 2.5V to 4.5V
		100	—	ns	VCC = 1.8V to 2.5V
CLK Rise Time	TR	—	2	μs	(Note 1)
CLK Fall Time	TF	—	2	μs	(Note 1)
Clock High Time	THI	150	—	ns	VCC = 4.5V to 5.5V
		250	—	ns	VCC = 2.5V to 4.5V
		475	—	ns	VCC = 1.8V to 2.5V
Clock Low Time	TLO	150	—	ns	VCC = 4.5V to 5.5V
		250	—	ns	VCC = 2.5V to 4.5V
		475	—	ns	VCC = 1.8V to 2.5V
Clock Delay Time	TCLD	50	—	ns	
Clock Enable Time	TCLE	50	—	ns	
Output Valid from Clock Low	TV	—	150	ns	VCC = 4.5V to 5.5V
		—	250	ns	VCC = 2.5V to 4.5V
		—	475	ns	VCC = 1.8V to 2.5V
Output Hold Time	THO	0	—	ns	(Note 1)
Output Disable Time	TDIS	—	200	ns	VCC = 4.5V to 5.5V (Note 1)
		—	250	ns	VCC = 2.5V to 4.5V (Note 1)
		—	500	ns	VCC = 1.8V to 2.5V (Note 1)
HOLD Setup Time	THS	100	—	ns	VCC = 4.5V to 5.5V
		100	—	ns	VCC = 2.5V to 4.5V
		200	—	ns	VCC = 1.8V to 2.5V
HOLD Hold Time	THH	100	—	ns	VCC = 4.5V to 5.5V
		100	—	ns	VCC = 2.5V to 4.5V
		200	—	ns	VCC = 1.8V to 2.5V
HOLD Low to Output High-Z	THZ	100	—	ns	VCC = 4.5V to 5.5V (Note 1)
		150	—	ns	VCC = 2.5V to 4.5V (Note 1)
		200	—	ns	VCC = 1.8V to 2.5V (Note 1)
HOLD High to Output Valid	THV	100	—	ns	VCC = 4.5V to 5.5V
		150	—	ns	VCC = 2.5V to 4.5V
		200	—	ns	VCC = 1.8V to 2.5V
Internal Write Cycle Time	TWC	—	5	ms	
Endurance	—	1M	—	E/W Cycles	(Note 2)

Note 1: This parameter is periodically sampled and not 100% tested.

2: This parameter is not tested but guaranteed by characterization. For endurance estimates in a specific application, please consult the Total Endurance Model which can be obtained on our website.

2.0 PIN DESCRIPTIONS

2.1 Chip Select (\overline{CS})

A low level on this pin selects the device. A high level deselects the device and forces it into standby mode. However, a programming cycle which is already initiated or in progress will be completed, regardless of the \overline{CS} input signal. If \overline{CS} is brought high during a program cycle, the device will go in standby mode as soon as the programming cycle is complete. As soon as the device is deselected, SO goes to the high impedance state, allowing multiple parts to share the same SPI bus. A low to high transition on \overline{CS} after a valid write sequence initiates an internal write cycle. After power-up, a low level on \overline{CS} is required prior to any sequence being initiated.

2.2 Serial Input (SI)

The SI pin is used to transfer data into the device. It receives instructions, addresses, and data. Data is latched on the rising edge of the serial clock.

2.3 Serial Output (SO)

The SO pin is used to transfer data out of the 25xx160. During a read cycle, data is shifted out on this pin after the falling edge of the serial clock.

2.4 Serial Clock (SCK)

The SCK is used to synchronize the communication between a master and the 25xx160. Instructions, addresses, or data present on the SI pin are latched on the rising edge of the clock input, while data on the SO pin is updated after the falling edge of the clock input.

2.5 Write Protect (\overline{WP})

This pin is used in conjunction with the WPEN bit in the status register to prohibit writes to the non-volatile bits in the status register. When \overline{WP} is low and WPEN is high, writing to the non-volatile bits in the status register is disabled. All other operations function normally. When \overline{WP} is high, all functions, including writes to the non-volatile bits in the status register operate normally. If the WPEN bit is set, \overline{WP} low during a status register write sequence will disable writing to the status register. If an internal write cycle has already begun, \overline{WP} going low will have no effect on the write.

The \overline{WP} pin function is blocked when the WPEN bit in the status register is low. This allows the user to install the 25xx160 in a system with \overline{WP} pin grounded and still be able to write to the status register. The \overline{WP} pin functions will be enabled when the WPEN bit is set high.

2.6 Hold (HOLD)

The \overline{HOLD} pin is used to suspend transmission to the 25xx160 while in the middle of a serial sequence without having to re-transmit the entire sequence over at a later time. It must be held high any time this function is not being used. Once the device is selected and a serial sequence is underway, the \overline{HOLD} pin may be pulled low to pause further serial communication without resetting the serial sequence. The \overline{HOLD} pin must be brought low while SCK is low, otherwise the HOLD function will not be invoked until the next SCK high to low transition. The 25xx160 must remain selected during this sequence. The SI, SCK, and SO pins are in a high impedance state during the time the part is paused and transitions on these pins will be ignored. To resume serial communication, \overline{HOLD} must be brought high while the SCK pin is low, otherwise serial communication will not resume. Lowering the \overline{HOLD} line at any time will tri-state the SO line.

3.0 FUNCTIONAL DESCRIPTION

3.1 PRINCIPLES OF OPERATION

The 25xx160 are 2048 byte Serial EEPROMs designed to interface directly with the Serial Peripheral Interface (SPI) port of many of today's popular microcontroller families, including Microchip's PIC16C6X/7X microcontrollers. It may also interface with microcontrollers that do not have a built-in SPI port by using discrete I/O lines programmed properly with the software.

The 25xx160 contains an 8-bit instruction register. The part is accessed via the SI pin, with data being clocked in on the rising edge of SCK. The \overline{CS} pin must be low and the \overline{HOLD} pin must be high for the entire operation. The \overline{WP} pin must be held high to allow writing to the memory array.

Table 3-1 contains a list of the possible instruction bytes and format for device operation. All instructions, addresses, and data are transferred MSB first, LSB last.

Data is sampled on the first rising edge of SCK after \overline{CS} goes low. If the clock line is shared with other peripheral devices on the SPI bus, the user can assert the \overline{HOLD} input and place the 25xx160 in 'HOLD' mode. After releasing the \overline{HOLD} pin, operation will resume from the point when the \overline{HOLD} was asserted.

3.2 Read Sequence

The part is selected by pulling \overline{CS} low. The 8-bit read instruction is transmitted to the 25xx160 followed by the 16-bit address, with the five MSBs of the address being don't care bits. After the correct read instruction and address are sent, the data stored in the memory at the selected address is shifted out on the SO pin. The data stored in the memory at the next address can be read sequentially by continuing to provide clock pulses. The internal address pointer is automatically incremented to the next higher address after each byte of data is shifted out. When the highest address is reached (07FFh), the address counter rolls over to address 0000h allowing the read cycle to be continued indefinitely. The read operation is terminated by raising the \overline{CS} pin (Figure 3-1).

3.3 Write Sequence

Prior to any attempt to write data to the 25xx160, the write enable latch must be set by issuing the WREN instruction (Figure 3-4). This is done by setting \overline{CS} low and then clocking out the proper instruction into the 25xx160. After all eight bits of the instruction are transmitted, the \overline{CS} must be brought high to set the write enable latch. If the write operation is initiated immediately after the WREN instruction without \overline{CS} being brought high, the data will not be written to the array because the write enable latch will not have been properly set.

Once the write enable latch is set, the user may proceed by setting the \overline{CS} low, issuing a write instruction, followed by the 16-bit address, with the five MSBs of the address being don't care bits, and then the data to be written. Up to 16 bytes of data can be sent to the 25xx160 before a write cycle is necessary. The only restriction is that all of the bytes must reside in the same page. A page address begins with XXXX XXXX XXXX 0000 and ends with XXXX XXXX XXXX 1111. If the internal address counter reaches XXXX XXXX XXXX 1111 and the clock continues, the counter will roll back to the first address of the page and overwrite any data in the page that may have been written.

For the data to be actually written to the array, the \overline{CS} must be brought high after the least significant bit (D0) of the n^{th} data byte has been clocked in. If \overline{CS} is brought high at any other time, the write operation will not be completed. Refer to Figure 3-2 and Figure 3-3 for more detailed illustrations on the byte write sequence and the page write sequence respectively. While the write is in progress, the status register may be read to check the status of the WPEN, WIP, WEL, BP1, and BP0 bits (Figure 3-6). A read attempt of a memory array location will not be possible during a write cycle. When the write cycle is completed, the write enable latch is reset.

TABLE 3-1: INSTRUCTION SET

Instruction Name	Instruction Format	Description
READ	0000 0011	Read data from memory array beginning at selected address
WRITE	0000 0010	Write data to memory array beginning at selected address
WRDI	0000 0100	Reset the write enable latch (disable write operations)
WREN	0000 0110	Set the write enable latch (enable write operations)
RDSR	0000 0101	Read status register
WRSR	0000 0001	Write status register

FIGURE 3-1: READ SEQUENCE

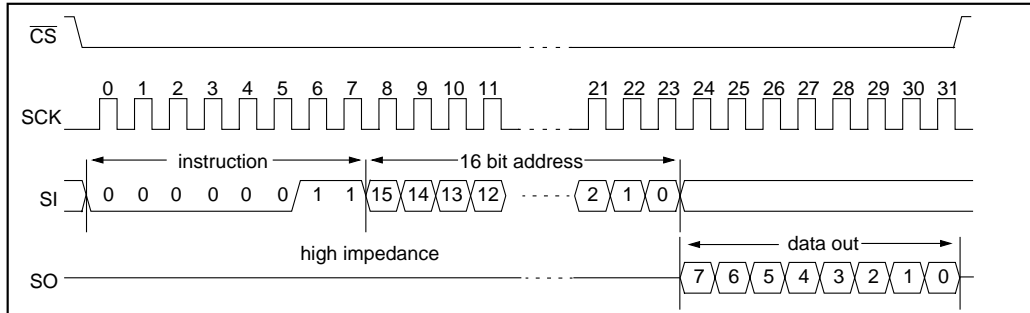


FIGURE 3-2: BYTE WRITE SEQUENCE

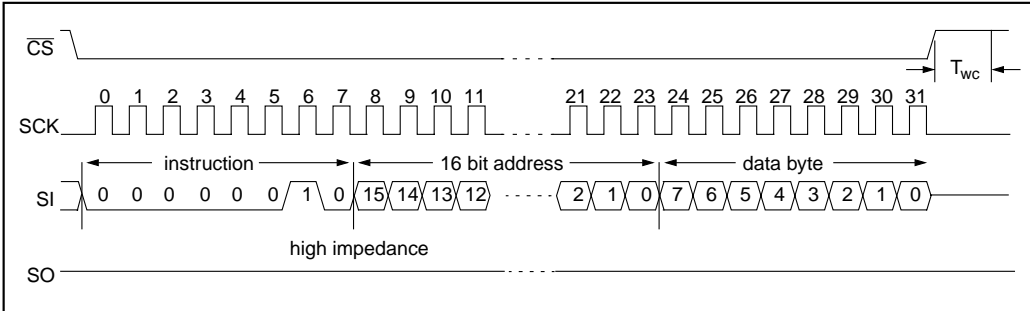
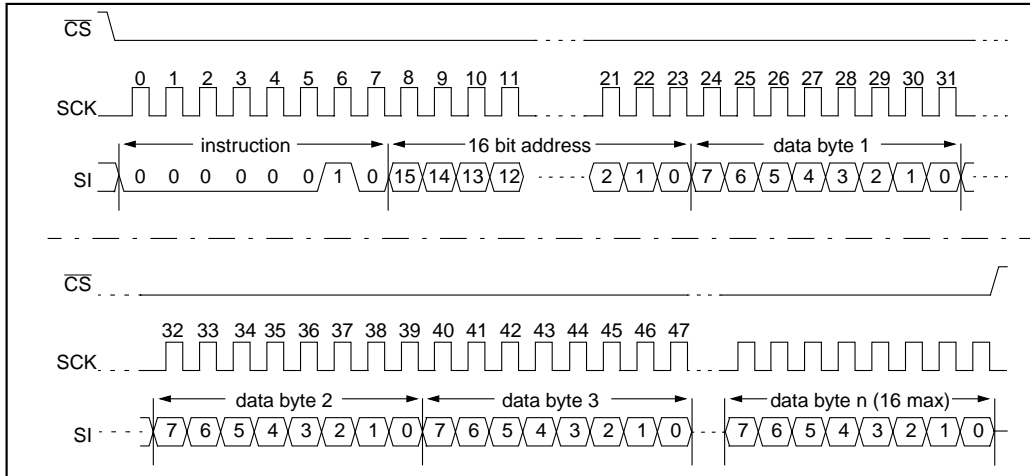


FIGURE 3-3: PAGE WRITE SEQUENCE



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3.4 Write Enable (WREN) and Write Disable (WRDI)

The 25xx160 contains a write enable latch. See Table 3-3 for the Write Protect Functionality Matrix. This latch must be set before any write operation will be completed internally. The WREN instruction will set the latch, and the WRDI will reset the latch.

The following is a list of conditions under which the write enable latch will be reset:

- Power-up
- WRDI instruction successfully executed
- WRSR instruction successfully executed
- WRITE instruction successfully executed

FIGURE 3-4: WRITE ENABLE SEQUENCE

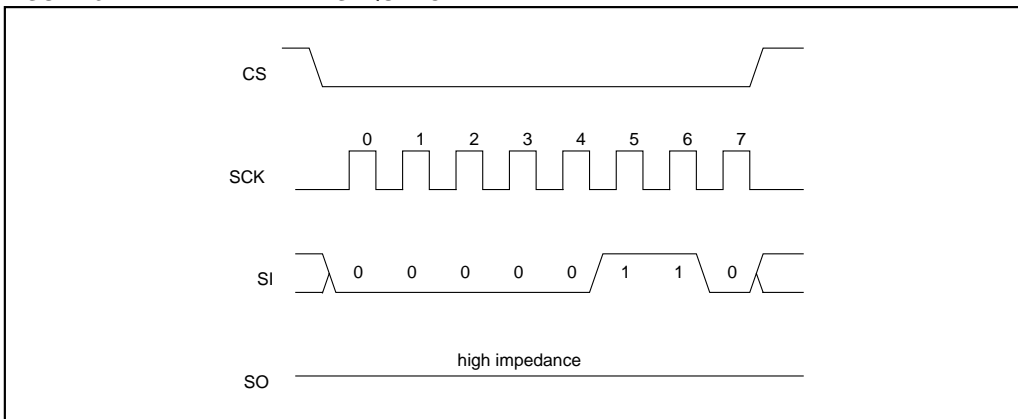
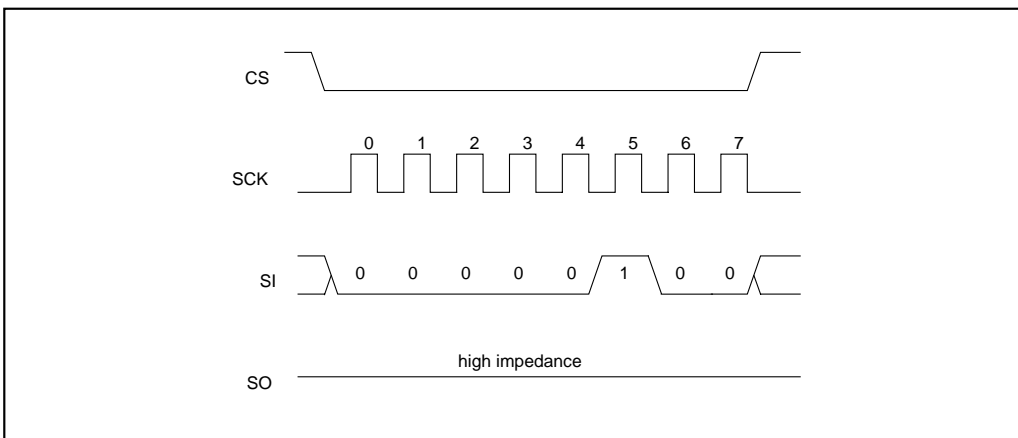


FIGURE 3-5: WRITE DISABLE SEQUENCE



3.5 Read Status Register (RDSR)

The RDSR instruction provides access to the status register. The status register may be read at any time, even during a write cycle. The status register is formatted as follows:

7	6	5	4	3	2	1	0
WPEN	X	X	X	BP1	BP0	WEL	WIP

The **Write-In-Process (WIP)** bit indicates whether the 25xx160 is busy with a write operation. When set to a '1' a write is in progress, when set to a '0' no write is in progress. This bit is read only.

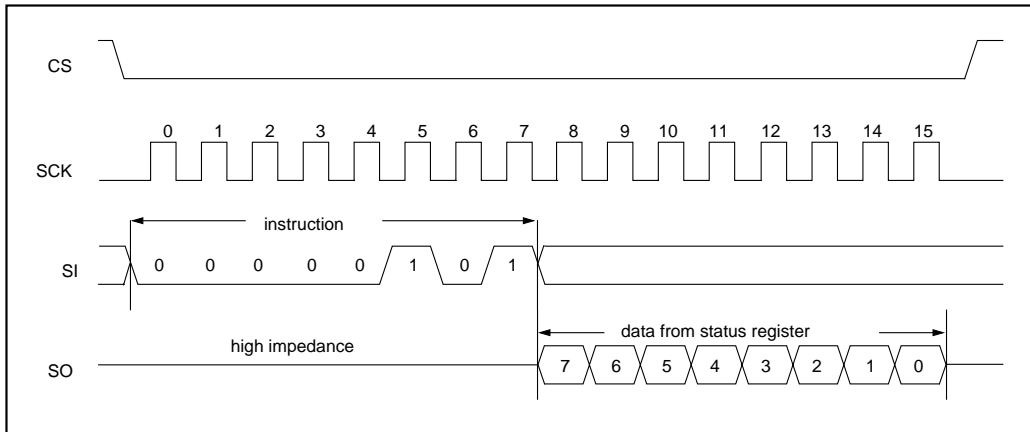
The **Write Enable Latch (WEL)** bit indicates the status of the write enable latch. When set to a '1' the latch allows writes to the array, when set to a '0' the latch

prohibits writes to the array. The state of this bit can always be updated via the WREN or WRDI commands regardless of the state of write protection on the status register. This bit is read only.

The **Block Protection (BP0 and BP1)** bits indicate which blocks are currently write protected. These bits are set by the user issuing the WRSR instruction. These bits are non-volatile.

See Figure 3-6 for the RDSR timing sequence.

FIGURE 3-6: READ STATUS REGISTER SEQUENCE



3.6 Write Status Register(WRSR)

The WRSR instruction allows the user to select one of four levels of protection for the array by writing to the appropriate bits in the status register. The array is divided up into four segments. The user has the ability to write protect none, one, two, or all four of the segments of the array. The partitioning is controlled as illustrated in Table 3-2.

The Write Protect Enable (WPEN) bit is a non-volatile bit that is available as an enable bit for the \overline{WP} pin. The Write Protect (\overline{WP}) pin and the Write Protect Enable (WPEN) bit in the status register control the programmable hardware write protect feature. Hardware write protection is enabled when \overline{WP} pin is low and the WPEN bit is high. Hardware write protection is disabled when either the \overline{WP} pin is high or the WPEN bit is low. When the chip is hardware write protected, only

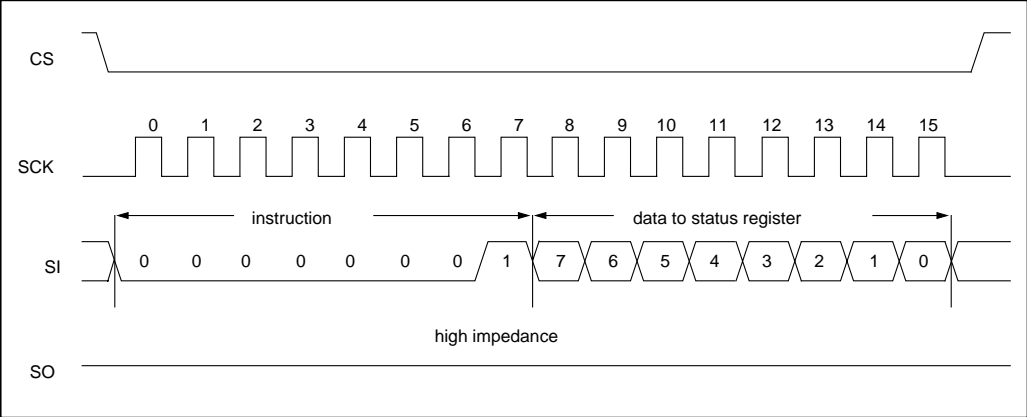
writes to non-volatile bits in the status register are disabled. See Table 3-3 for a matrix of functionality on the WPEN bit.

See Figure 3-7 for the WRSR timing sequence.

TABLE 3-2: ARRAY PROTECTION

BP1	BP0	Array Addresses Write Protected
0	0	none
0	1	upper 1/4 (0600h - 07FFh)
1	0	upper 1/2 (0400h - 07FFh)
1	1	all (0000h - 07FFh)

FIGURE 3-7: WRITE STATUS REGISTER SEQUENCE



3.7 Data Protection

The following protection has been implemented to prevent inadvertent writes to the array:

- The write enable latch is reset on power-up.
- A write enable instruction must be issued to set the write enable latch.
- After a byte write, page write, or status register write, the write enable latch is reset.
- \overline{CS} must be set high after the proper number of clock cycles to start an internal write cycle.
- Access to the array during an internal write cycle is ignored and programming is continued.

3.8 Power On State

The 25xx160 powers on in the following state:

- The device is in low power standby mode ($\overline{CS} = 1$).
- The write enable latch is reset.
- SO is in high impedance state.
- A low level on \overline{CS} is required to enter active state.

TABLE 3-3: WRITE PROTECT FUNCTIONALITY MATRIX

WPEN	WP	WEL	Protected Blocks	Unprotected Blocks	Status Register
X	X	0	Protected	Protected	Protected
0	X	1	Protected	Writable	Writable
1	Low	1	Protected	Writable	Protected
X	High	1	Protected	Writable	Writable

NOTES:

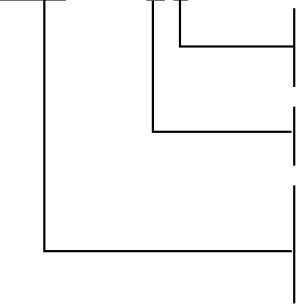
NOTES:

NOTES:

25AA160/25LC160/25C160

25AA160/25LC160/25C160 PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office..

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	Package: P = Plastic DIP (300 mil Body), 8-lead SN = Plastic SOIC (150 mil Body) ST = TSSOP, 8-lead OT = SOT-23, 5 lead
	Temperature Range: Blank = 0°C to +70°C I = -40°C to +85°C E = -40°C to +125°C
	Device: 24AA00 128 bit 1.8V I ² C Serial EEPROM 24AA00T 128 bit 1.8V K I ² C Serial EEPROM (Tape and Reel) 24LC00 128 bit 2.5V I ² C Serial EEPROM 24LC00T 128 bit 2.5V K I ² C Serial EEPROM (Tape and Reel) 24C00 128 bit 5.0V I ² C Serial EEPROM 24C00T 128 bit 5.0V K I ² C Serial EEPROM (Tape and Reel)

Sales and Support

Data Sheets

Products supported by a preliminary Data Sheet may have an errata sheet describing minor operational differences and recommended workarounds. To determine if an errata sheet exists for a particular device, please contact one of the following:

1. Your local Microchip sales office
2. The Microchip Corporate Literature Center U.S. FAX: (602) 786-7277
3. The Microchip's Bulletin Board, via your local CompuServe number (CompuServe membership NOT required).

Please specify which device, revision of silicon and Data Sheet (include Literature #) you are using.

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Microchip received ISO 9001 Quality System certification for its worldwide headquarters, design, and wafer fabrication facilities in January, 1997. Our field-programmable PICmicro™ 8-bit MCUs, Serial EEPROMs, related specialty memory products and development systems conform to the stringent quality standards of the International Standard Organization (ISO).